ABSTRACT OF THE DISCLOSURE

ETCH WITH INCREASED MASK SELECTIVITY

A method for etching features in an etch layer in a plasma processing chamber is provided. An etch gas is flowed into the plasma processing chamber. A top outer electrode is maintained at a temperature of at least 150° C during the etching of the features. The etch gas is formed into a plasma, which etches the etch layer.

FIG. 1

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